Synthesis and Characterization of Gallium Silylamido Complexes

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The reaction between GaCl₃ and 1 equiv of HN(SiMe₂Ph)₂ in CH₂Cl₂ solution affords colorless crystals of [Cl₂-Ga{ μ -N(H)SiMe₂Ph}]₂ (1). The related reaction between GaCl₃ and 1 equiv of LiN(SiMe₂Ph)₂ in hexane solution results in the isolation of colorless crystals of [PhGa{N(SiMe₂Ph)₂}(μ -Cl)]₂ (2). In contrast, treatment of GaCl₃ with 1 equiv of N(SiMe₃)₃ in CH₂Cl₂ solutions affords colorless crystals of [MeGaCl₂]₂ (4). Compounds 2 and 4 are the result of monochloride substitution and transfer of a phenyl and methyl ligand, respectively, from the silyl group of the amine to the Ga center. All the complexes have been characterized by X-ray crystallography.

Introduction

Gallium nitride (GaN) is a technologically important material because of its semiconducting properties, thermal stability, and resistance to chemical attack.1 GaN has a band gap of 3.4 eV and is therefore suitable for use in a range of optoelectronic devices, such as blue-light-emitting diodes.² Bulk GaN may be prepared via the reaction of either Ga₂O₃³ or Ga⁴ metal with ammonia at high temperatures. Alternatively, thin films of GaN can be prepared via dual-source chemical vapor deposition (CVD) of R_3Ga (R = Me, Et) and ammonia.¹ However, this route requires high reaction temperatures (>900 °C) and huge overpressures of ammonia (as great as 10⁴). Single-source precursors, which contain preformed Ga-N bonds, offer several potential advantages over these traditional routes. Possible advantages include lower deposition temperatures, reduced contamination from carbon, and removal of the inefficient use of ammonia. A further advantage of single-source precursors is the possibility of forming unusual phases, for example, cubic GaN.⁵ A number of single-source precursors to GaN have been reported previously.^{1,6} The list includes $[Ga(N_3)_3(py)_3]^7$ $[N_{3}{Me_{2}N}_{2}Ga{\mu-NMe_{2}}]_{2},^{8} [H_{2}GaNH_{2}]_{3},^{5} [Ga{N(SiMe_{3})_{2}}-$

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 $(OSiMe_3)_2py]$,⁹ $[(N_3)_2Ga\{(CH_2)_3NMe_2\}]$,¹⁰ and $[H_2GaN_3]_n$.¹¹ However, there are problems associated with these compounds, including the stability of the precursor and the quality of the GaN produced. Consequently there is a need for new Ga–N compounds.

Dehalosilylation reactions (i.e., the elimination of Me₃SiX) have been employed in the synthesis of relatively pure samples of GaAs and InAs at low temperatures.¹² Recently, this method was extended to dehydrosilylation reactions (involving the elimination of Me₃SiH) for the preparation of GaP, GaAs, AlP, and AlAs nanoparticles.¹³ We are interested in developing gallium silylamido complexes as CVD precursors to GaN. These complexes should reduce the possibility of contamination from species such as carbon in the resulting films and address some of the foregoing problems.

In this paper, we report the synthesis and structures of two gallium silylamido complexes, $[Cl_2Ga\{\mu-N(H)SiMe_2Ph\}]_2$ (1) and $[PhGa\{N(SiMe_2Ph)_2\}(\mu-Cl)]_2$ (2). The structure of $[MeGaCl_2]_2$ (4) is also described. The formation of compounds 2 and 4 is the result of a phenyl and methyl group transfer, respectively, from the silyl group of the amide to the gallium center.

Results and Discussion

The reaction between GaCl₃ and HN(SiMe₂Ph)₂ at -78 °C in CH₂Cl₂ resulted, after workup, in a 63% yield of colorless crystalline **1** (Scheme 1). Analytical and spectroscopic data for **1** were consistent with the formulation [Cl₂Ga{N(H)SiMe₂Ph}]₂. The dimeric nature of **1** was confirmed by an X-ray crystal-

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Figure 1. Molecular structure of **1**. The transannular Ga····Ga separation is 2.803(1) Å.

Scheme 1



 Table 1. Selected Bond Lengths (Å) and Angles (deg) for 1

Ga-Cl(1)	2.1380(13)	Ga-Cl(2)	2.1540(14)
Ga-N	1.988(4)	Ga-N'	1.968(3)
Si-N	1.801(4)		
N-Ga-N'	89.74(14)	N-Ga-Cl(1)	110.55(11)
N'-Ga-Cl(1)	115.86(11)	N-Ga-Cl(2)	114.88(11)
N'-Ga-Cl(2)	110.73(11)	Cl(1)-Ga-Cl(2)	113.12(6)
Si-N-Ga	120.1(2)	Si-N-Ga'	127.2(2)
Ga-N-Ga'	90.26(14)		

lographic study which shows it to be centrosymmetric with a planar Ga₂N₂ ring and *trans* dimethylphenylsilyl groups (Figure 1). The bond lengths and angles within the Ga₂N₂Cl₄ core (Table 1) and to the silyl substituents are virtually identical to those seen in [Cl₂Ga{ μ -N(H)SiMe₃}]₂.¹⁴ The Ga₂N₂ ring is very nearly square, with the Ga–N–Ga and N–Ga–N angles being, within statistical significance, 90°, though there is a small asymmetry in the nitrogen bridge, with the Ga–N distances being 1.968-(3) and 1.988(4) Å (there is a similar asymmetry in the structure of [Cl₂Ga{ μ -N(H)SiMe₃}]₂). The transannular Ga···Ga separation [2.803(1) Å] lies at the short end of Ga···Ga separations in similarly bridged species (the separation in the trimethyl species is 2.810 Å¹⁴). The N–Si bond [1.801(4) Å] is the same as in [Cl₂Ga{ μ -N(H)SiMe₃}]₂, but significantly longer than observed in, for example, [Me(Cl)Ga{ μ -N(H)SiMe₃}]₂¹⁵ [1.744





Figure 2. Molecular structure of 2. The transannular Ga····Ga separation is 3.411(1) Å.

Å] and $[Me_2Ga{\mu-N(Si(H)Me_2)_2}]_2^{16}$ [av 1.770 Å]. There are no major intermolecular packing interactions of note, though there is evidence for a weak stacking interaction between the phenyl rings of symmetry-related molecules which have a mean interplanar separation of 3.75 Å and a centroid…centroid distance of 4.35 Å. The shortest intermolecular Cl·…Cl distance is 3.45 Å.

The mutually *trans* arrangement of the bridging N(H)SiMe₂-Ph groups we observe in **1** is also seen in the solid-state structures of all other known dimeric silylamidogallanes.^{14–18} However, the NMR data for compound **1** indicated that in solution, mixtures of *trans*-[Cl₂Ga{ μ -N(H)SiMe₂Ph}]₂ and *cis*-[Cl₂Ga{ μ -N(H)SiMe₂Ph}]₂ were present (*trans:cis* = 1:1). A similar *trans*-*cis* isomerization was reported for the dimeric silylamidogallanes described previously.^{14–18}

With a view to preparing a gallium silylamide, of the type $[Cl_2Ga{N(SiR_3)_2}]_n$, the reaction of GaCl₃ with a lithiated silylamine was carried out. Accordingly, GaCl3 was reacted with 1 equiv of LiN(SiMe₂Ph)₂ at -78 °C in hexanes (Scheme 1). A colorless crystalline product was obtained by cooling a hexane solution of 2 to -20 °C. Analytical and spectroscopic data for 2 were consistent with the formation of $[PhGa{N(SiMe_2Ph)_2}]$ - $(\mu$ -Cl)]₂ rather than the expected product [Cl₂Ga{N(SiMe₂- $Ph_{2}]_{2}$ (3). The structure of 2 was confirmed by X-ray crystallography and is seen to have approximate molecular C_2 symmetry (about an axis perpendicular to the Ga₂Cl₂ plane) that is broken only by the differently skewed orientations of the gallium-bound phenyl rings (Figure 2). The [N(SiMe₂Ph)₂] groups are oriented cis with respect to the Ga₂Cl₂ ring, which has a nonplanar geometry, being slightly folded (by ca. 13°) about the Cl···Cl vector. This structure is, to the best of our knowledge, the only reported example of a bis(amino)substituted Ga₂Cl₂ ring system, the closest related structure being that of an indium complex,¹⁹ where the amino groups are *trans*. The dimensions of the Ga₂Cl₂ core (Table 2) are very similar to those observed in $[Cy_2Ga(\mu-Cl)]_2^{20}$ (Cy = cyclohexyl), having a transannular Ga····Ga separation of 3.411(1) Å (cf. 3.38 Å in

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Table 2. Selected Bond Lengths (Å) and Angles (deg) for 2

Ga(1)-Cl(1)	2.3587(9)	Ga(1)-Cl(2)	2.3813(8)
Ga(1) - N(1)	1.850(3)	Ga(1) - C(6)	1.952(2)
Ga(2)-Cl(1)	2.4025(8)	Ga(2)-Cl(2)	2.3651(9)
Ga(2) - N(2)	1.846(2)	Ga(2) - C(28)	1.957(2)
Si(1) - N(1)	1.739(3)	Si(2) - N(1)	1.738(3)
Si(3)-N(2)	1.738(3)	Si(4)-N(2)	1.740(3)
N(1)-Ga(1)-C(6)	130.04(11)	N(1)-Ga(1)-Cl(1)	111.27(9)
C(6)-Ga(1)-Cl(1)	105.73(9)	N(1)-Ga(1)-Cl(2)	106.62(8)
C(6)-Ga(1)-Cl(2)	107.12(7)	Cl(1)-Ga(1)-Cl(2)	87.89(3)
N(2)-Ga(2)-C(28)	132.93(11)	N(2)-Ga(2)-Cl(2)	109.80(9)
C(28)-Ga(2)-Cl(2)	103.97(7)	N(2)-Ga(2)-Cl(1)	106.68(8)
C(28)-Ga(2)-Cl(1)	106.76(7)	Cl(2)-Ga(2)-Cl(1)	87.25(3)
Ga(1)-Cl(1)-Ga(2)	91.50(3)	Ga(2)-Cl(2)-Ga(1)	91.87(3)

the cyclohexyl species). In both complexes the N–Ga–C angles are substantially enlarged from tetrahedral, being 130.0(1)° and 132.9(1)° at Ga(1) and Ga(2), respectively, in **2**, and 132.4° in $[Cy_2Ga(\mu-Cl)]_2$,²⁰ enlargements that are very much greater than those observed in, for example, **1**, where the Cl(1)–Ga–Cl(2) angle is only 113.1(1)°. The Ga–N distances [Ga(1)-N(1) = 1.850(3) Å, Ga(2)-N(2) = 1.846(2) Å] are both significantly shorter than those seen in, for example, $[(\eta^1-Cp^*)Ga\{N(SiMe_3)_2\}-(\mu-N_3)]_2^{21}$ (Cp* = pentamethylcyclopentadienyl), where the Ga–N distance is 1.872 Å. There are no noteworthy intermolecular packing interactions.

The isolation of compound **2** is surprising and is a result of a monochloride substitution and transfer of a phenyl ligand from the [N(SiMe₂Ph)₂] group to the Ga center. The mechanism for the formation of **2** is not known. However, related methyl group transfers have been observed previously for indium and antimony compounds.^{22,23} If the reaction between GaCl₃ and 2 equiv of LiN(SiMe₂Ph)₂ is carried out, the result is the same; however, compound **2** was formed in a higher yield. It is interesting to note that a phenyl ligand rather than a methyl ligand transfers from the [N(SiMe₂Ph)₂] group in the reaction described herein. The NMR data for compound **2** indicated that in solution, mixtures of *cis*-[PhGa{N(SiMe₂Ph)₂}(μ -Cl)]₂ and *trans*-[PhGa{N(SiMe₂Ph)₂}(μ -Cl)]₂ were present.

The reaction between GaCl₃ and 1 equiv of N(SiMe₃)₃ in CH₂Cl₂ at -78 °C resulted, after workup, in a light brown oil. Cooling of this oil to -20 °C overnight afforded colorless crystalline 4 (Scheme 1). Spectroscopic and analytical data indicated, however, that a product of, or similar to, the anticipated formula $[Cl_xGaN(SiMe_3)_{3-x}]_n$ (x = 1-3) had not been formed. The nature of the crystalline material was established by X-ray crystallography and found to be dimeric with the formula $[MeGaCl_2]_2$ (4). The structure of 4 revealed that individual [MeGaCl₂] units are associated into centrosymmetric dimers via bridging chlorine interactions (Figure 3), the molecule having (excluding the methyl hydrogen atoms) both molecular and crystallographic C_{2h} symmetry. Each gallium is four-coordinate with a severely distorted tetrahedral geometry. The Ga₂Cl₂ core is planar, and the internal ring angles at gallium and chlorine are 88.89(6)° and 91.11(6)°, respectively (Table 3). As expected, the terminal Ga-Cl bond distance of 2.1547-(9) Å is shorter than the bridging Ga-Cl bond distance [2.3324-(12) Å]. The Cl(1)–Ga–C(1) angle is significantly enlarged from tetrahedral at 127.0(3)°, a value closer to the analogous

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Figure 3. Molecular structure of **4** (90% probability ellipsoids). The transannular Ga····Ga separation is 3.3304(15) Å.



Figure 4. Part of the pseudo cubic close-packed array of molecules present in the crystals of 4, showing the ABC sequence layers.

Table 3. Bond Lengths (Å) and Angles (°) for 4

Ga-C(1) Ga-Cl(2)	1.928(7) 2.3324(12)	Ga-Cl(1)	2.1547(19)
C(1)-Ga-Cl(1) Cl(1)-Ga-Cl(2) Ga'-Cl(2)-Ga(1)	127.0(3) 103.83(4) 91.11(6)	$\begin{array}{c} C(1)-Ga-Cl(2)\\ Cl(2')-Ga-Cl(2) \end{array}$	113.17(17) 88.89(6)

angle observed in 2 than that seen in 1. The structure of 4 is related to the aluminum analogue [MeAlCl₂]₂, which has a similar dimeric structure.²⁴ The packing of molecules of **4** is a classic cubic close-packed arrangement with hexagonal layers of molecules lying in the crystallographic *ab* plane stacked in an ABCABC fashion (Figure 4); the interlayer separation is 5.82 Å. The isolation of compound 4 was surprising and is a result of a monochloride substitution and transfer of a methyl group from the amine $[N(SiMe_3)_3]$ to the gallium center. This is similar to the phenyl transfer observed in the formation of compound 2, although in this reaction a chloride was not substituted for an amide ligand. Interestingly, the formation of [MeGaCl₂]₂ from the reaction of GaCl₃ with [Me₂SiO]₄, (Me₃Si)₂O, Me₃SiOLi, or Me₄Si has been described previously.²⁵ The colorless crystals were difficult to isolate from the light brown oil, and so the NMR spectrum of 4 shows a number of peaks in the region 0.42-0.62 ppm. However, a number of peaks are also expected due to the possible formation of isomers in solution (e.g., trans-[MeGaCl₂]₂ and *cis*-[MeGaCl₂]₂).

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In summary, the gallium silylamido complexes $[Cl_2Ga_{N(SiMe_2Ph)_2}]_2$ (1) and $[PhGa\{N(SiMe_2Ph)_2\}(\mu-Cl)]_2$ (2) have been synthesized and structurally characterized. In addition, the reaction of GaCl₃ with N(SiMe₃)₃ led to the formation of [MeGaCl₂]₂ (4), which was structurally characterized. The formation of 2 and 4 involved unusual transfer of phenyl and methyl groups, respectively, from the silyl ligand to the Ga center. Unfortunately, the low volatility of compound 2 and the presence of a Ga–C bond precluded thin film growth by CVD. However, preliminary investigations of compound 1 have shown that it can serve as a precursor to GaN, the details of which will be described in a future publication.

Experimental Section

General Procedures. All manipulations were performed under a dry, oxygen-free dinitrogen atmosphere using standard Schlenk techniques or in a Mbraun Unilab glovebox. All solvents were distilled from appropriate drying agents prior to use (sodium—ether and hexanes; CaH₂ for CH₂Cl₂). All other reagents were procured commercially from Aldrich and used without further purification. Microanalytical data were obtained at the University College London (UCL).

Physical Measurements. NMR spectra were recorded on a Brüker AMX400 spectrometer at UCL, referenced to CD₂Cl₂, which was dried and degassed over molecular sieves prior to use; ¹H and ¹³C chemical shifts are reported relative to SiMe₄ (δ 0.00). Mass spectra (CI) were run on a micromass ZABSE instrument and IR spectra on a Shimadzu FTIR-8200 instrument. Melting points were obtained in sealed glass capillaries under nitrogen and are uncorrected.

Synthesis of 1. A solution of HN(SiMe₂Ph)₂ (1.64 mL, 5.68 mmol) in CH₂Cl₂ (10 mL) was added slowly to a stirred solution of GaCl₃ (1.00 g, 5.68 mmol) in CH₂Cl₂ (15 mL) at -78 °C. A white precipitate formed immediately, and the reaction mixture was allowed to warm slowly to room temperature over a 1 h period. The resulting colorless solution was reduced in vacuo to a volume of approximately 10 mL. Cooling of this solution to -20 °C afforded colorless crystals of 1 after a few days. These crystals were redissolved in ether (5 mL) and cooled to -20 °C. X-ray-quality crystals of 1 were obtained after a few weeks at this temperature (63% yield). Mp: 104-107 °C. ¹H NMR (CD₂Cl₂): δ 0.78 (s, SiCH₃), 0.82 (s, SiCH₃), 2.41 (s, NH), 7.00-7.39 (m, SiC₆ H_5). ¹³C{¹H} NMR (CD₂Cl₂): δ 1.16 (s, SiCH₃), 3.10 (s, SiCH₃), 127.9, 128.4 (s, *m*-SiC₆H₅), 129.3, 131.0 (s, *p*-SiC₆H₅), 133.7, 133.9 (s, o-SiC₆H₅), 134.4 (s, *ipso*-SiC₆H₅). IR (KBr disk, cm⁻¹): 2957 m, 1428 s, 1258 s, 1180 m, 1116 vs, 1051 m, 998 w, 933 s, 831 vs, 800 vs, 748 m, 699 vs, 687 w, 594 w, 471 w.

Synthesis of 2. A solution of ⁿBuLi (1.78 mL, 2.84 mmol; 1.6 M in hexane) was added dropwise to a cooled (-78 °C) solution of HN-(SiMe₂Ph)₂ (0.82 mL, 2.84 mmol) in hexanes (10 mL) with stirring. A white precipitate formed after a few minutes, and the mixture was stirred for 2 h. The slurry was then added dropwise to a cooled (-78 °C) solution of GaCl₃ (0.5 g, 2.84 mmol) in hexanes (10 mL). The mixture was allowed to warm slowly to room temperature with stirring. After this time the reaction mixture was filtered through Celite to give a pale yellow solution. Cooling of this solution to -20 °C afforded colorless crystals of **2** after a few weeks (20% yield). The reaction between 2 equiv of LiN(SiMe₂Ph)₂ with GaCl₃ resulted in a 40% yield of compound **2**. ¹H NMR (CD₂Cl₂): δ 0.17 (s, SiCH₃), 0.25 (s, SiCH₃), 7.20–7.63 (m, SiC₆H₅ and GaC₆H₅). ¹³C{¹H} NMR (CD₂Cl₂): δ 1.6,

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Table 4. Crystallographic Data for Compounds 1, 2, and 4

	1	2	4
empirical formula	$C_{16}H_{24}N_2Si_2Cl_4Ga_2$	$C_{44}H_{54}N_2Si_4Cl_2Ga_2$	C ₂ H ₆ Cl ₄ Ga ₂
fw	581.8	933.6	311.3
space group	<i>C</i> 2/ <i>c</i> (no. 15)	$P\overline{1}$ (no. 2)	<i>C</i> 2/ <i>m</i> (no. 12)
T (°C)	-90	-100	-173
a (Å)	12.530(1)	10.296(1)	11.999(2)
b (Å)	14.472(2)	13.970(1)	6.737(1)
c (Å)	13.457(1)	17.756(1)	7.218(1)
α (deg)		73.50(1)	
β (deg)	93.85(1)	83.42(1)	126.20(1)
γ (deg)		75.59(1)	
$V(Å^3)$	2434.8(4)	2369.2(3)	470.8(1)
Z	4 ^a	2	2^b
p _{calcd}	1.587	1.309	2.196
$(g \text{ cm}^{-3})$			
λ (Å)	0.71073	1.54178	0.71073
$\mu (\text{mm}^{-1})$	2.76	3.64	6.77
$R1^c$	0.040	0.037	0.054
$wR2^d$	0.086	0.087	0.152

^{*a*} The molecule has crystallographic C_i symmetry. ^{*b*} The molecule has crystallographic C_{2i} symmetry. ^{*c*} R1 = $\sum ||F_o| - |F_c||/\sum |F_o|$. ^{*d*} wR2 = $\{\sum [w(F_o^2 - F_c^2)^2]/\sum [w(F_o^2)^2]\}^{1/2}$; $w^{-1} = \sigma^2(F_o^2) + (aP)^2 + bP$.

2.7 (s, SiCH₃), 126.1, 126.5 (s, m-SiC₆H₅), 131.9, 132.3 (s, p-SiC₆H₅), 140.8, 142.0 (s, o-SiC₆H₅), 128.3, 128.5 (s, m-GaC₆H₅), 131.4, 131.6 (s, p-GaC₆H₅), 140.2, (s, o-GaC₆H₅), *ipso*-carbon not detected. IR (KBr disk, cm⁻¹): 2957 m, 2899 w, 1483 w, 1427 s, 1406 w, 1302 w, 1258 vs, 1180 w, 1112 s, 1022 s, 999 w, 947 s, 868 vs, 798 vs, 729 s, 700 s, 648 w, 522 w, 472 w, 449 w, 407 w.

Synthesis of 4. A solution of N(SiMe₃)₃ (0.66 g, 2.84 mmol) in CH₂Cl₂ (10 mL) was added dropwise to a cooled (-78 °C) solution of GaCl₃ (0.50 g, 2.84 mmol) in 10 mL of CH₂Cl₂ with stirring. The reaction temperature was maintained at -78 °C for 1 h, and the mixture was allowed to warm slowly to room temperature. During this time a color change occurred from colorless to light straw, and the mixture was stirred at 40 °C for 30 min. The solvent was removed in vacuo, and the resulting light brown oil was dissolved in CH₂Cl₂ (2 mL). Cooling of this solution to -20 °C overnight afforded colorless crystals of **4**. Anal. Calcd for CH₃Cl₂Ga (carried out on oil): C, 7.72; H, 1.94; Cl, 45.55. Found: C, 9.39; H, 2.40; Cl, 41.32. ¹H NMR (CDCl₃): δ 0.416–0.624 (m, CH₃). ¹³C{¹H} NMR (CDCl₃): δ 3.23, 2.91, 2.06, 1.78, 1.62.

X-ray Crystallography. Table 4 provides a summary of the crystallographic data for compounds 1, 2, and 4. CCDC 171272 to 171274.

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Supporting Information Available: ORTEP diagrams and X-ray crystallographic files in CIF format for the structures of compounds 1, 2, and 4. This material is available free of charge via the Internet at http://pubs.acs.org.

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